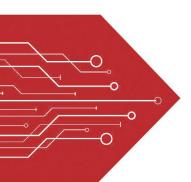
MSKSEMI















ESD

TVS

TSS

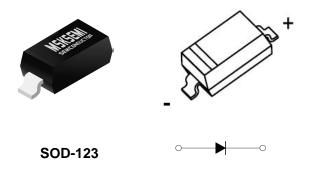
MOV

GDT

PLED

Broduct data sheet





Schottky Barrier Diode

FEATURES

- Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection
- Negligible Reverse Recovery Time
- Low Capacitance

MARKING:

SD103AW:S4	SD103BW:S5	SD103CW:S6
- II S4 III +	-IIIS5 III+	-IIIS6 III+

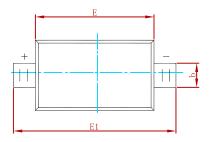
MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

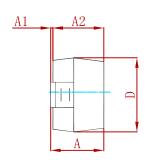
Symbol	Parameter		I I m i 4		
Symbol	Farameter	SD103AW	SD103BW	SD103CW	Unit
V _{RRM}	Peak Repetitive Reverse Voltage	40	30	20	
V _{RWM}	Working Peak Reverse Voltage	40	30	20	V
V _{R(RMS)}	RMS Reverse Voltage	28	21	14	V
I _{FM}	Forward Continuous Current	350		mA	
I _{FSM}	Non-repetitive Peak Forward Surge Current@t=8.3ms	2		Α	
P _D	Power Dissipation	400		mW	
R _{OJA}	Thermal Resistance from Junction to Ambient	250		°C/W	
Tj	Junction Temperature 125			$^{\circ}$	
T _{stg}	Storage Temperature	-55~+150		$^{\circ}$	

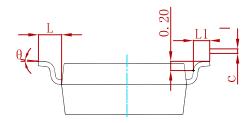
ELECTRICAL CHARACTERISTICS(T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions		Min	Тур	Max	Unit	
		I _R =100μA	SD103AW	40				
Reverse voltage	$V_{(BR)}$		SD103BW	30			V	
			SD103CW	20				
Reverse current	I _R	V _R =30V	SD103AW			5	μА	
		V _R =20V	SD103BW					
		V _R =10V	SD103CW					
Forward voltage	V _F	I _F =20mA				0.37	V	
		I _F =200mA				0.6		
Total capacitance	C _{tot}	V _R =0V,f=1MHz			50		pF	
Reverse recovery time	t _{rr}	I _F = I _R =200mA, I _{rr} =	:0.1×I _R , R _L =100Ω		10		ns	

PACKAGE MECHANICAL DATA

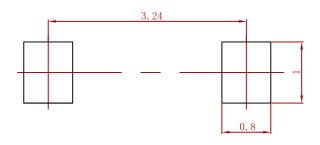






Cumbal	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.450	0.650	0.018	0.026	
С	0.080	0.150	0.003	0.006	
D	1.500	1.700	0.059	0.067	
E	2.600	2.800	0.102	0.110	
E1	3.550	3.850	0.140	0.152	
L	0.500 REF		0.020 REF		
L1	0.250	0.450	0.010	0.018	
θ	0°	8°	0°	8°	

Suggested Pad Layout



Note:

- 1. Controlling dimension: in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
SD103AW-SD103CW	SOD-123	3000



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